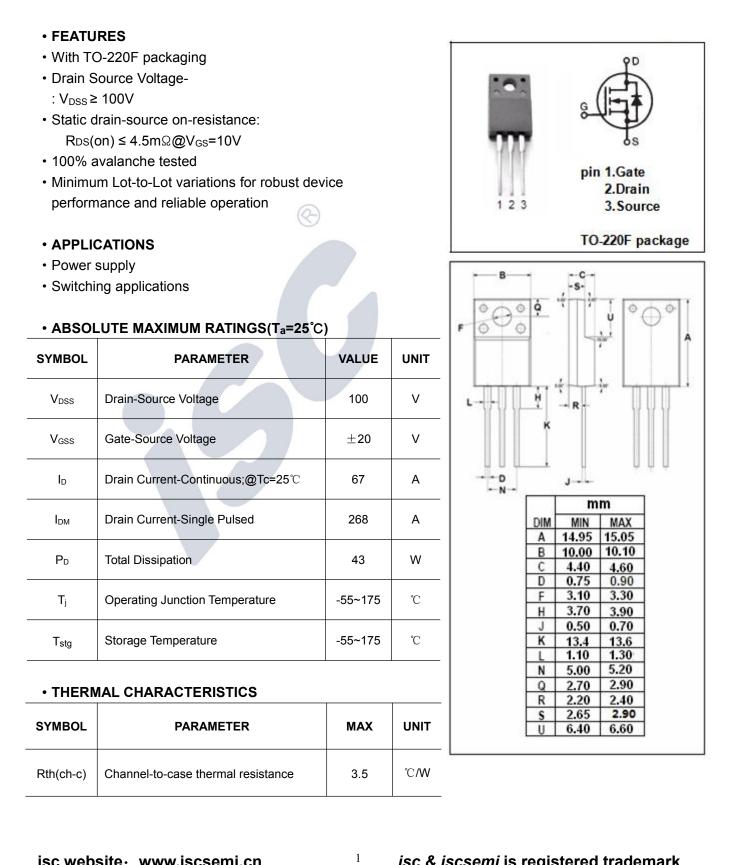


INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

FDPF045N10A





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FDPF045N10A

ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 250uA	100			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =250uA	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 67A			4.5	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 80V; V _{GS} = 0V V _{DS} = 80V; V _{GS} = 0V;T _J =150°C			1 500	μA
VSDF	Diode forward voltage	I _{SD} = 67A, V _{GS} = 0 V			1.3	V

NOTICE:

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